SHI LI G® 浙江世菱半导体有限公司
ZHEJIANG SHILING SEMICONDUCTOR CO.,LTD.

Specifcation of products

：

：MFK200U4K1

ZHEJIANG SHILING SEMICONDUCTOR CO.,LTD.

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PRODUCT FEATURES

- Ultrafast Recovery Time
- Low Recovery Loss
- Low Forward Voltage
- Low Leakage Current
- Low Inductance Package



APPLICATIONS

- Inversion Welder
- Uninterruptible Power Supply
- Plating Power Supply
- Ultrasonic Cleaner and Welder
- Converter & Chopper
- PFC

ABSOLUTE MAXIMUM RATINGS

T_C=25℃ unless otherwise specified

Symbol	Parameter/Test Conditions		Values	Unit
V_R	Maximum D.C. Reverse Voltage		400	V
V_{RRM}	Maximum Repetitive Reverse Voltage			
$I_{F(AV)}$	Average Forward Current	T_C=100℃, Per Diode	100	A
		T_C=100℃ , Per Moudle	200	
$I_{F(RMS)}$	RMS Forward Current	T_C=100℃, Per Diode	140	
I_{FSM}	Non Repetitive Surge Forward Current	T_J=45℃,t=10ms,Sine,peak value	1300	
		T_J=45℃,t=8.3ms,Sine,peak value	1360	
I^2t	For Fusing	T_J=45℃,t=10ms,Sine,peak value	7900	A^2S
		T_J=45℃,t=8.3ms,Sine,peak value	7700	
P_D	Power Dissipation		538	W
T_J	Junction Temperature		-40 to +150	℃
T_{STG}	Storage Temperature Range		-40 to +125	℃
Torque	Module to Sink	Recommended（M6）	3～5	Nm
Torque	Module Electrodes	Recommended（M6）	3～5	Nm
R_{thJC}	Junction to Case Thermal Resistance(Per Diode)		0.22	℃/W
Weight				g

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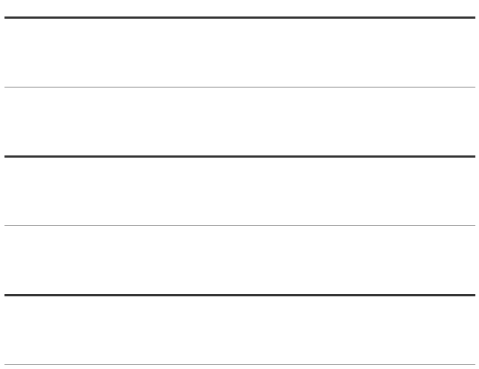

Figure 5.Forward current vs Case temperature

Figure 6. Transient Thermal Impedance